ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE622
Silicon Rectifier, General Purpose, High Voltage, Fast Recovery (Surface Mount)

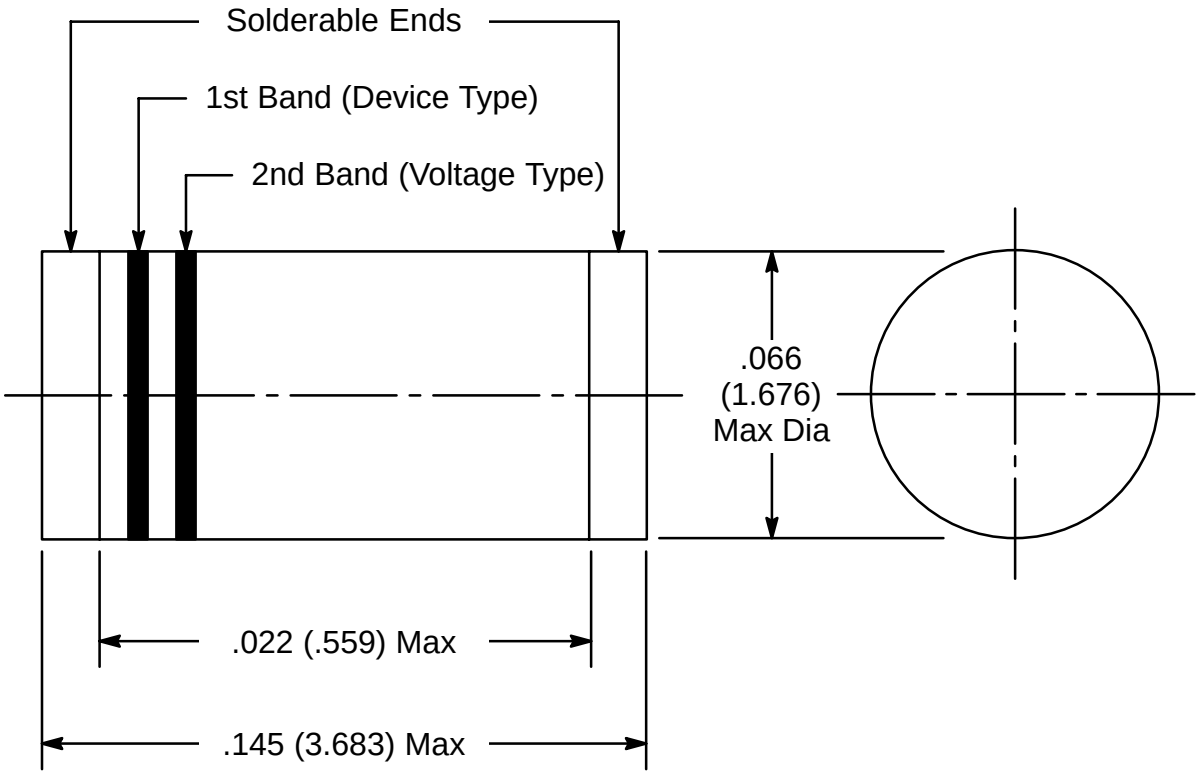
Features:

- High Temperature Metallurgically Bonded
- Glass Passivated Junction
- High Temperature Soldering Guaranteed:
  +450°C/5 Seconds at Terminals. Complete Device Submersible Temperature of +260°C/10 Seconds in Solder Bath.

Maximum Ratings and Electrical Characteristics: (T_A = +25°C unless otherwise specified. 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.)

Maximum Recurrent Peak Reverse Voltage, V_{RRM} 400V
Maximum RMS Voltage, V_{RMS} 280V
Maximum DC Blocking Voltage, V_{DC} 400V
Maximum Average Forward Rectified Current (T_T = +75°C), $I_{T(AV)}$ 0.5A
Peak Forward Surge Current, I_{FSM}
(8.3ms Single Half Sine–Wave Superimposed on Rated Load) 10A
Maximum Instantaneous Forward Voltage (I_T = 0.5A), V_F 1.2V
Maximum DC Reverse Current (V_{DC} = 400V), I_R
T_A = +25°C 5µA
T_A = +125°C 50µA
Maximum Reverse Recovery Time (T_J = +25°C, Note 1), t_{rr} 50ns
Typical Junction Capacitance (Note 2), C_J 4pF
Operating Junction Temperature Range, T_J . . . . . –65° to +175°C
Storage Temperature Range, T_{stg} . . . . . –65° to +175°C
Maximum Thermal Resistance, Junction–to–Terminal (Note 3), R_{thJL} . . . . . 70°C/W
Maximum Thermal Resistance, Junction–to–Ambient (Note 4), R_{thJA} . . . . . 150°C/W

Note 1. Reverse Recovery Test Conditions: I_F = 0.5A, I_R = 1A, I_{RR} = 0.25A..
Note 2. Measured at 1MHz and applied reverse voltage of $4V_{DC}$.
Note 2. Thermal resistance, junction–to–terminal, 5.0mm^2 copper pads to each terminal.
Note 3. Thermal resistance, junction–to–ambient, 5.0mm^2 copper pads to each terminal.



Two Bands Indicates Cathode